

Title of Change:	Hydrazine elimination in ON Semiconductor Niigata Co., Ltd., Japan (OSNC).				
Proposed first ship date:	22 August 2019				
Contact information:	Contact your local ON Semiconductor Sales Office	or < <u>Tetsuya.Fukushima@onsemi.com</u> >			
Samples:	Contact your local ON Semiconductor Sales Office .				
Type of notification:	This is an Initial Product/Process Change Notification (IPCN) sentto customers. IPCNs are issued at least 30 days prior to the issuance of the Final Change Notice (FPCN). An IPCN is an advance notification about an upcoming change and contains general information regarding the change details and devices affected. It also contains the preliminary reliability qualification plan. The completed qualification and characterization data will be included in the Final Product/Process Change Notification (FPCN). This IPCN notification will be followed by a Final Product/Process Change Notification (FPCN) at least 90 days prior to implementation of the change. In case of questions, contact <pcn.support@onsemi.com>.</pcn.support@onsemi.com>				
Change Part Identification:	Date Code				
Change category:	🖾 Wafer Fab Change 🔲 Assembly Change 🔲 Test Change 🔲 Other				
Change Sub-Category(s):       Image: Manufacturing Site Change/Addition         Manufacturing Process Change       Product specific change		<ul> <li>Datasheet/Product Doc change</li> <li>Shipping/Packaging/Marking</li> <li>Other:</li></ul>			
Sites Affected:	ON Semiconductor Sites: ON Niigata, Japan	External Foundry/Subcon Sites: None			
Description and Purpose: This Initial notification announces the elimination of Hydrazine in ON Semiconductor Niigata Co., Ltd. Japan for parts listed in this PCN. Hydrazine was identified as a prohibited chemical in ON Semiconductor as it is considered as a carcinogenic substance and has high risk offire and explosion. The related products are transferred to a process that does not use Hydrazine on the same site, ON Semiconductor Niigata, Japan (OSNC).					
	Before Change Description	After Change Description			
Fab ON Niigata, Japan (OSNC)	N1 Fab (Minimum rule=0.8um, Class=100)	N1 Fab (Minimum rule=0.8um, Class=100) AND N2 Fab (Minimum rule=0.25um, Class=10)			
Wire material	Aluminum (without Anti-reflected Layer)	Aluminium (with Anti-reflected Layer)			
Interlayer material	Silicon nitride and Polyimide or Polyimide	Silicon nitride and Silicon oxide or Oxide			
	Silicon nitride and Polyimide	Silicon nitride and Silicon oxide			



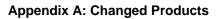
## **Qualification Plan:**

QV DEVICE NAME:	LB11870-TRM-E
PACKAGE:	HSSOP48 (375 mil)

Test	Specification	Condition	Interval
HTOL	JESD22-A108	Tj=150°C, 100 % max rated Vcc	1008 hrs
HTSL	JESD22-A103	Ta= 150°C	1008 hrs
ТС	JESD22-A104	Ta= -65°C to +150°C	500 сус
ТНВ	JESD22-A101	85°C, 85% RH, bias	1008 hrs
uHAST	JESD22-A118	130°C, 85% RH, 18.8psig,	96 hrs
PC	J-STD-020 JESD-A113	MSL 3 @ 260 °C	-
HBM	JS001	100pF,1.5kohm	-
CDM	JS002		-

## List of Affected Standard Parts

Part Number	Qualification Vehicle	
LB11600JV-TLM-E		
LB11988V-TLM-E		
LB11988HR-TLM-E	LB11870-TRM-E	
LB1838JM-TRM-E		



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Product	Customer Part Number	Qualification Vehicle
LB11600JV-TLM-E		LB11870-TRM-E
LB11988HR-TLM-E		LB11870-TRM-E
LB11988V-TLM-E		LB11870-TRM-E
LB1838JM-TRM-E		LB11870-TRM-E